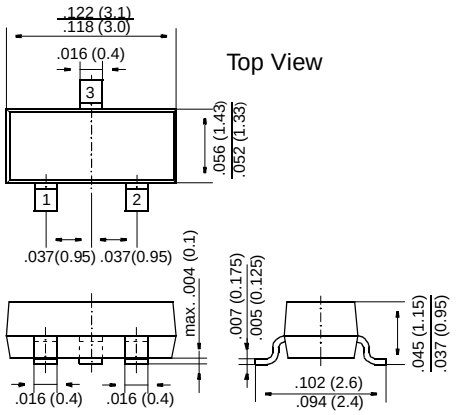
BS828

DMOS Transistors (N-Channel)

SOT-23



Dimensions in inches and (millimeters)

Pin configuration
1 = Gate, 2 = Source, 3 = Drain

FEATURES

- High breakdown voltage
- High input impedance
- High-speed switching
- No minority carrier storage time
- CMOS logic compatible input
- No thermal runaway
- No secondary breakdown
- Specially suited for telephone subsets

MECHANICAL DATA

Case: SOT-23 Plastic Package
Weight: approx. 0.008 g
Marking
S28

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	240	V
Drain-Gate Voltage	V_{DGS}	240	V
Gate-Source Voltage (pulsed)	V_{GS}	± 20	V
Drain Current (continuous)	I_D	230	mA
Power Dissipation at T_{SB} = 50 °C	P_{tot}	0.310[1)]	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_S	–65 to +150	°C
[1)] Device on fiberglass substrate, see layout			

Inverse Diode

	Symbol	Value	Unit
Max. Forward Current (continuous) at T_{amb} = 25 °C	I_F	0.3	A
Forward Voltage Drop (typ.) at V_{GS} = 0, I_F = 0.3 A, T_j = 25 °C	V_F	0.85	V

GENERAL SEMICONDUCTOR®

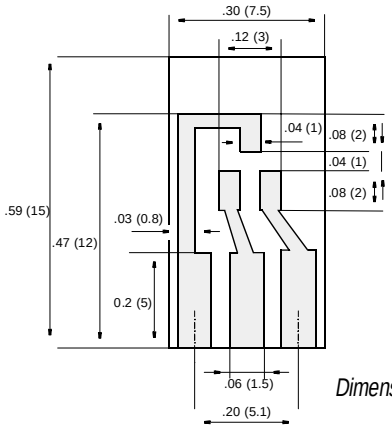
BS828

ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage at I_D = 100 µA, V_{GS} = 0	$V_{(BR)DSS}$	240	250	–	V
Gate-Body Leakage Current at V_{GS} = 15 V, V_{DS} = 0	I_{GSS}	–	–	10	nA
Drain Cutoff Current at V_{DS} = 130 V, V_{GS} = 0 at V_{DS} = 70 V, V_{GS} = 0.2 V	 I_{DSS} I_{DSX}	 – –	 – –	 1 25	 µA µA
Gate-Source Threshold Voltage at V_{GS} = V_{DS}, I_D = 1 mA	$V_{GS(th)}$	–	1.5	2.5	V
Drain-Source ON Resistance at V_{GS} = 2.8 V, I_D = 100 mA	$R_{DS(ON)}$	–	5.5	8	Ω
Thermal Resistance Junction to Substrate Backside	R_{thSB}	–	–	320[1)]	K/W
Thermal Resistance Junction to Ambient Air	R_{thJA}	–	–	450[1)]	K/W
Capacitances at V_{DS} = 20 V, V_{GS} = 0, f = 1 MHz Input Capacitance Output Capacitance Feedback Capacitance	 C_{iss} C_{oss} C_{rss}	 – – –	 80 20 5	 – – –	 pF pF pF
Switching Times at V_{GS} = 10 V, V_{DS} = 10 V, R_D = 100 Ω Turn-On Time Turn-Off Time	 t_{on} t_{off}	 – –	 5 50	 – –	 ns ns

[1)] Device on fiberglass substrate, see layout



Dimensions in inches (millimeters)

Layout for R_{thJA} test

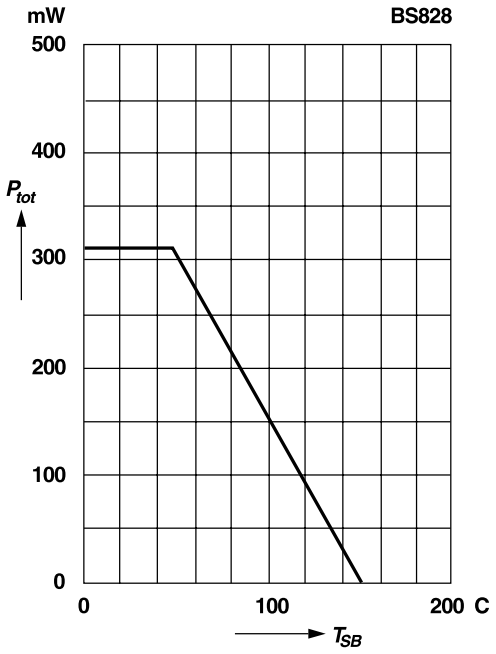
Thickness: Fiberglass 0.059 in (1.5 mm)
Copper leads 0.012 in (0.3 mm)

GENERAL SEMICONDUCTOR®

RATINGS AND CHARACTERISTIC CURVES BS828

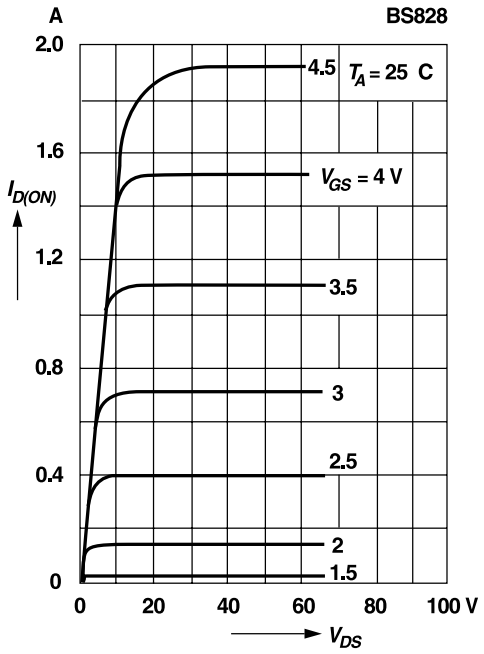
Admissible power dissipation versus temperature of substrate backside

Device on fiberglass substrate, see layout



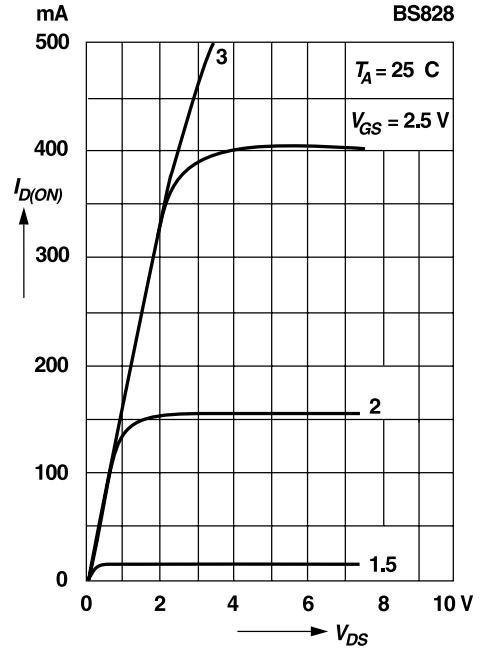
Output characteristics

Pulse test width 80 ms; pulse duty factor 1%

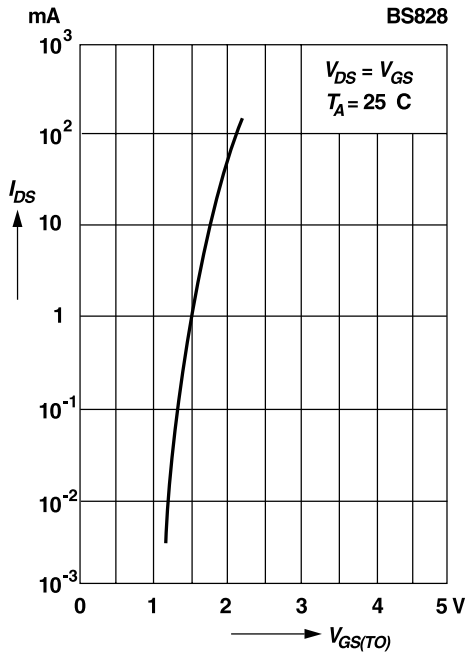


Saturation characteristics

Pulse test width 80 ms; pulse duty factor 1%



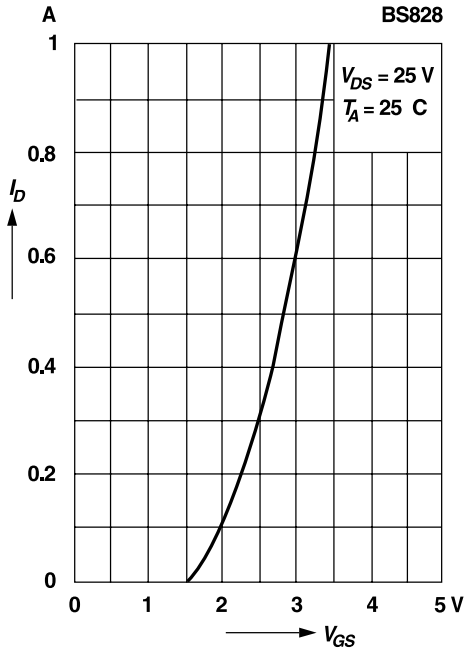
Drain-source current versus gate threshold voltage



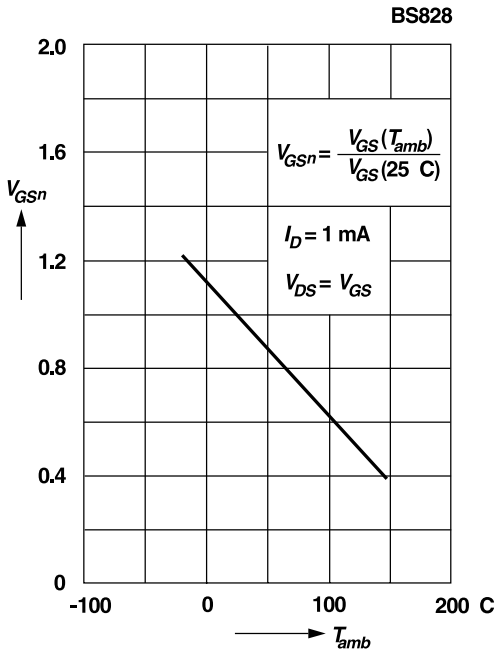
GENERAL SEMICONDUCTOR®

Drain current versus gate-source voltage

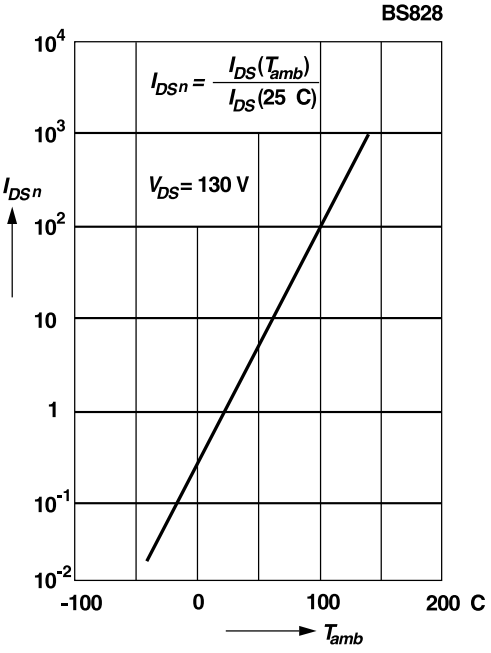
Pulse test width 80 ms; pulse duty factor 1%



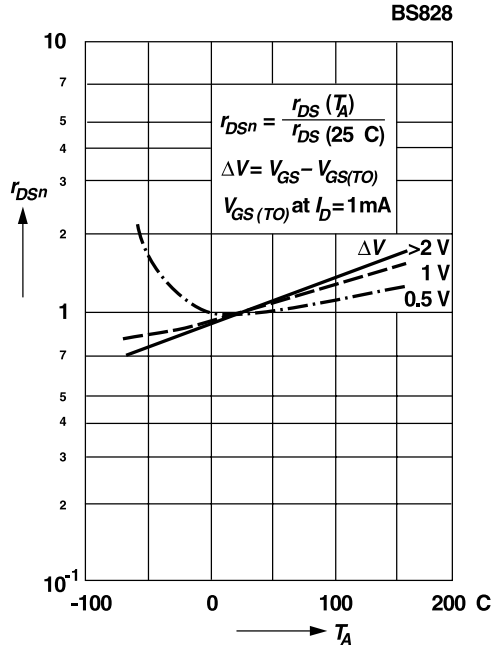
Normalized gate-source voltage versus temperature



Normalized drain-source current versus temperature

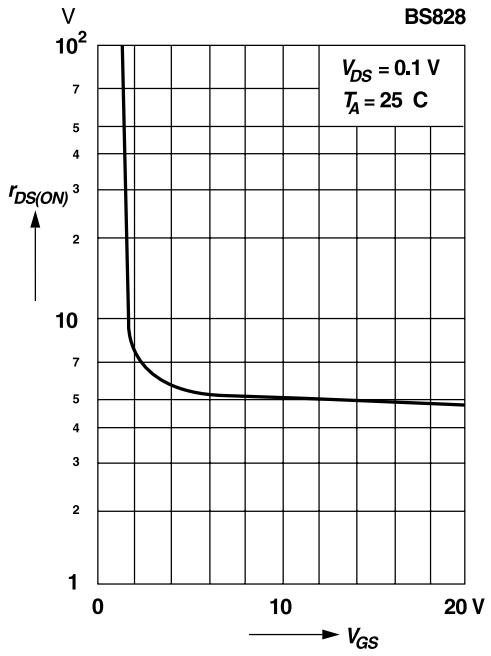


Normalized drain-source resistance versus temperature



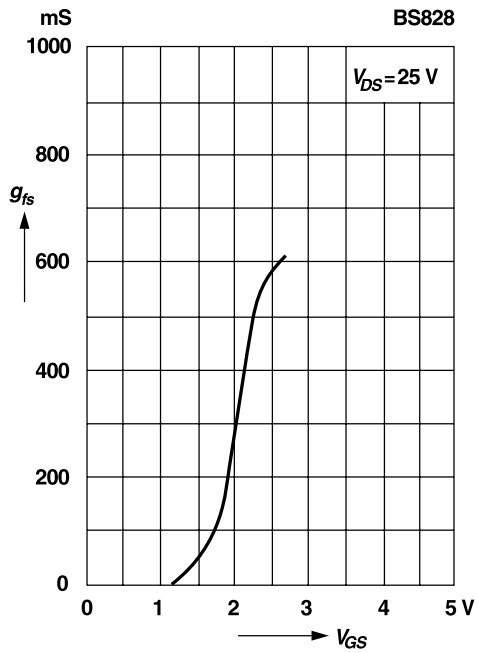
GENERAL SEMICONDUCTOR®

Drain-source resistance versus gate-source voltage



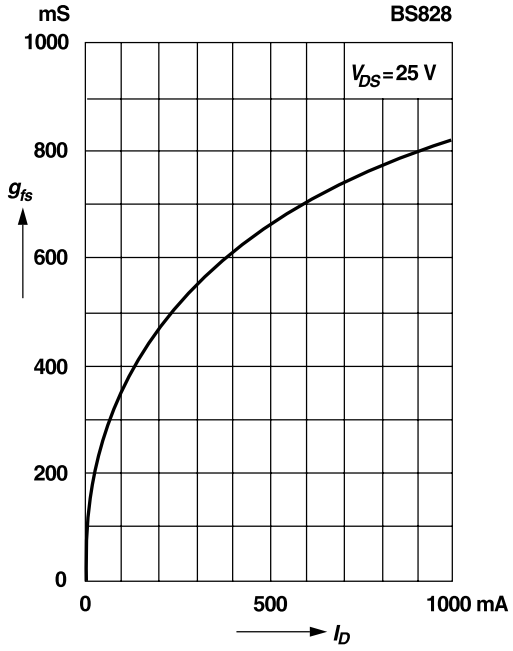
Transconductance versus gate-source voltage

Pulse test width 80 ms; pulse duty factor 1%



Transconductance versus drain current

Pulse test width 80 ms; pulse duty factor 1%



littlediode
COMPONENTS FOR ALL

Littlediode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

LittleDiode.com

Looking forward to providing you with the best possible service.